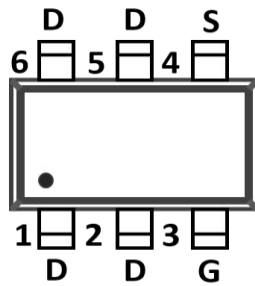
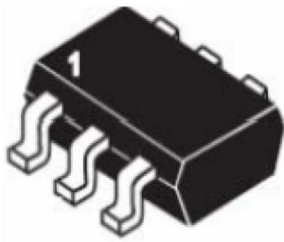
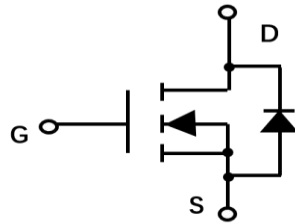


N-Channel Enhancement Mode Field Effect Transistor



SOT-23-6L



Product Summary

- V_{DS} 100V
- I_D 3.0A
- $R_{DS(ON)}$ (at $V_{GS}=10V$) <120mohm
- $R_{DS(ON)}$ (at $V_{GS}=4.5V$) <140mohm

General Description

- Trench Power MV MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$

Applications

- DC-DC Converters
- Power management functions

■ Absolute Maximum Ratings ($T_A=25^{\circ}C$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		V_{DS}	100	V
Gate-source Voltage		V_{GS}	± 20	V
Drain Current	$T_A=25^{\circ}C$	I_D	3	A
	$T_A=70^{\circ}C$		2.4	
Pulsed Drain Current ^A		I_{DM}	12	A
Single Pulse Avalanche Energy		E_{AS}	8	mJ
Total Power Dissipation @ $T_A=25^{\circ}C$		P_D	1.5	W
Thermal Resistance Junction-to-Ambient ^B		$R_{\theta JA}$	83	$^{\circ}C/W$
Thermal Resistance From Junction To Lead		$R_{\theta JL}$	36	$^{\circ}C/W$
Junction and Storage Temperature Range		T_J, T_{STG}	-55~+150	$^{\circ}C$

■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJS03N10A	F2	1003	3000	30000	120000	7"



YJS03N10A

■ Electrical Characteristics (T_J=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D =250μA	100			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V, V _{GS} =0V			1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} =0V			±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D =250μA	1.1	1.8	3.0	V
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} = 10V, I _D =3A		95	120	mΩ
		V _{GS} = 4.5V, I _D =2.4A		100	140	
Diode Forward Voltage	V _{SD}	I _S =3A, V _{GS} =0V		0.8	1.2	V
Maximum Body-Diode Continuous Current	I _S				3	A
Dynamic Parameters						
Input Capacitance	C _{iss}	V _{DS} =50V, V _{GS} =0V, f=1MHZ		1070		pF
Output Capacitance	C _{oss}			33		
Reverse Transfer Capacitance	C _{rss}			30		
Switching Parameters						
Total Gate Charge	Q _g	V _{GS} =10V, V _{DS} =50V, I _D =10A		26		nC
Gate-Source Charge	Q _{gs}			5.4		
Gate-Drain Charge	Q _{gd}			5.8		
Reverse Recovery Charge	Q _{rr}	I _F =10A, di/dt=100A/us		30.1		ns
Reverse Recovery Time	t _{rr}			40		
Turn-on Delay Time	t _{D(on)}	V _{GS} =10V, V _{DD} =50V, R _L =6.4Ω R _{GEN} =3Ω		7		
Turn-on Rise Time	t _r			24		
Turn-off Delay Time	t _{D(off)}			24		
Turn-off fall Time	t _f			31		

A. Pulse Test: Pulse Width ≤ 300us, Duty cycle ≤ 2%.

B. R_{θJA} is the sum of the junction-to-lead and lead-to-ambient thermal resistance, where the lead thermal reference is defined as the solder mounting surface of the drain pins. R_{θJL} is guaranteed by design, while R_{θJA} is determined by the board design. The maximum rating presented here is based on mounting on a 1 in 2 pad of 2oz copper.

■ Typical Performance Characteristics

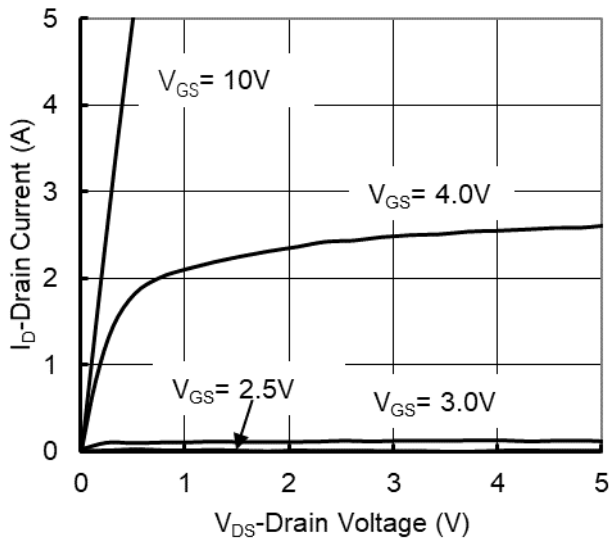


Figure 1. Output Characteristics

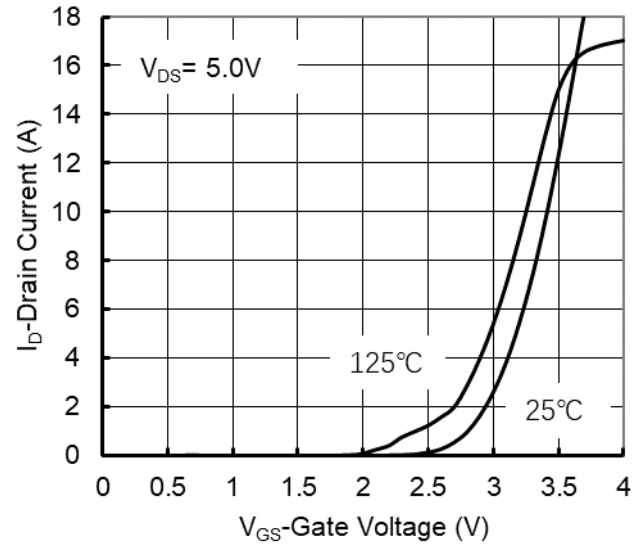


Figure 2. Transfer Characteristics

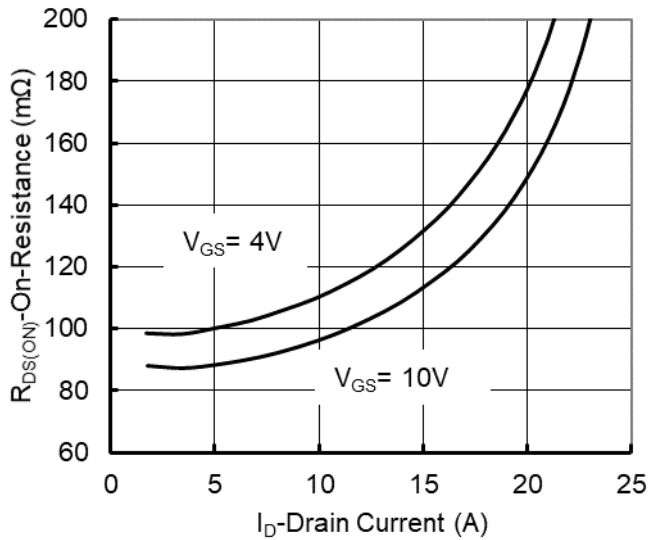


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

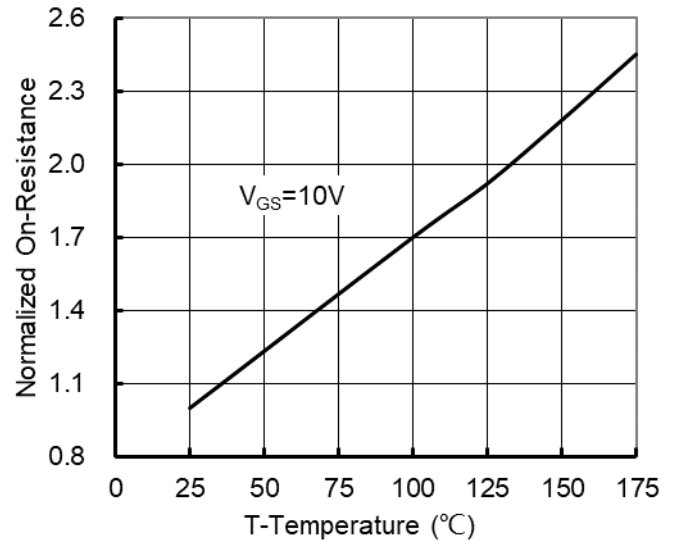


Figure 4. On-Resistance vs. Junction Temperature

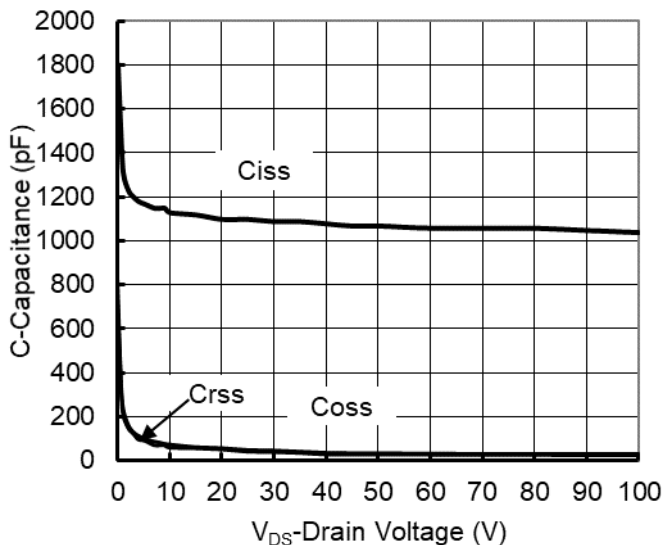


Figure 5. Capacitance Characteristics

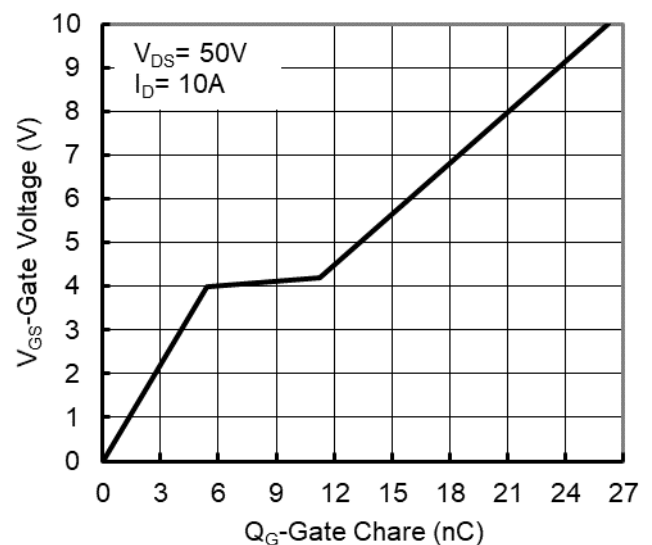


Figure 6. Gate Charge

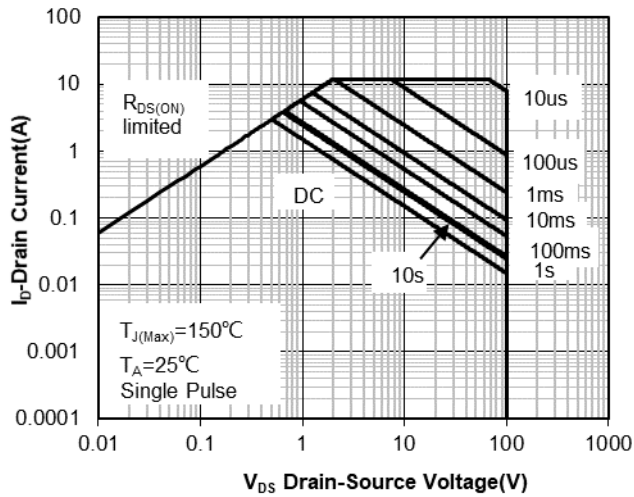


Figure 7. Safe Operation Area

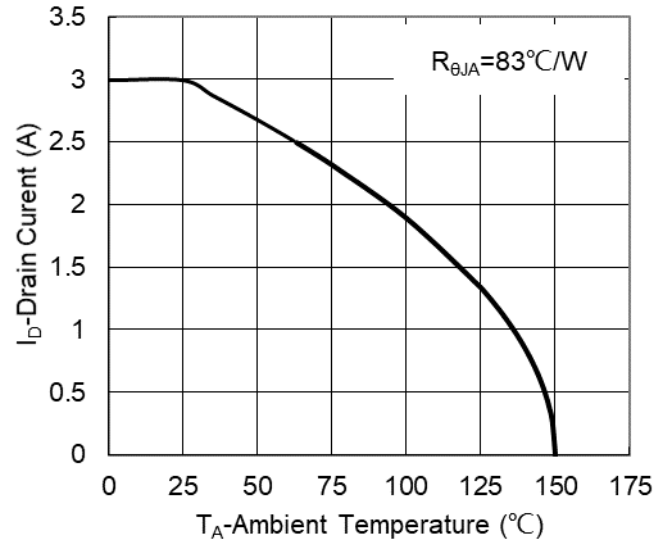


Figure 8. Maximum Continuous Drain Current vs Ambient Temperature

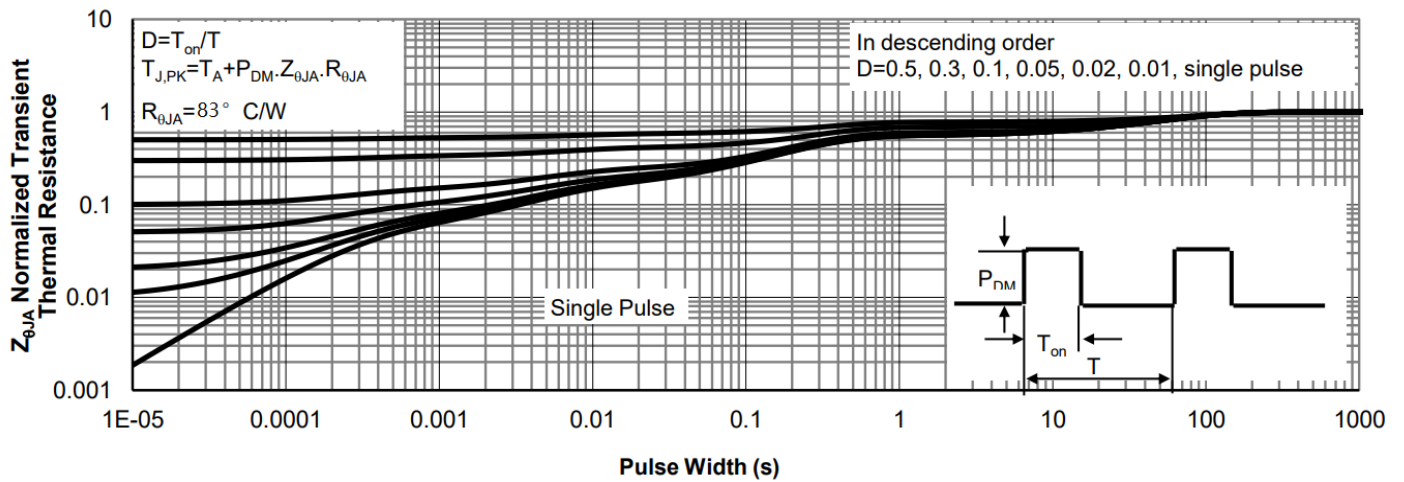
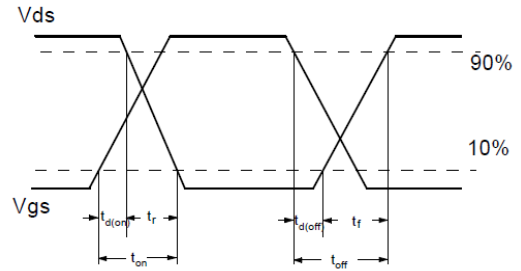
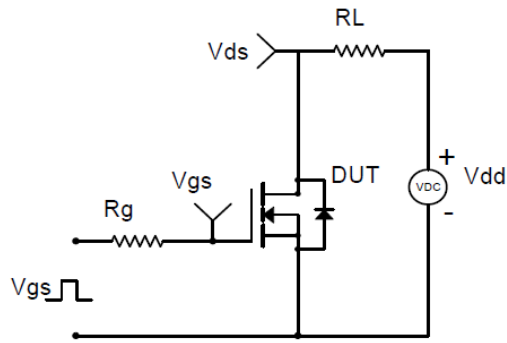
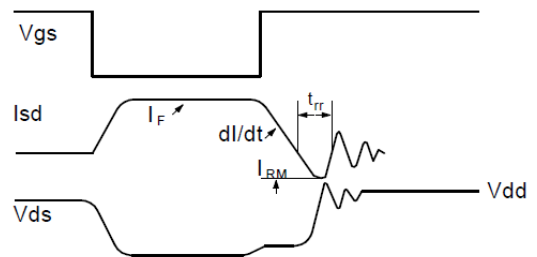
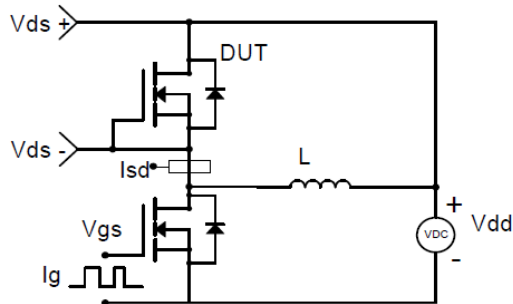


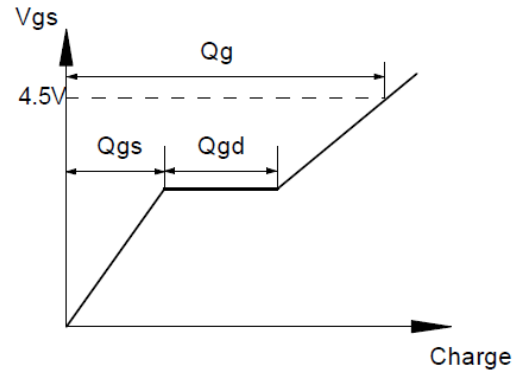
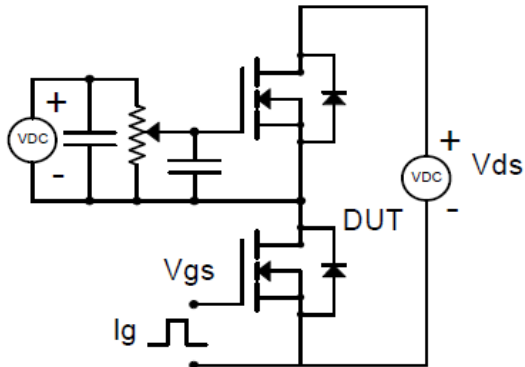
Figure 9. Normalized Maximum Transient Thermal Impedance



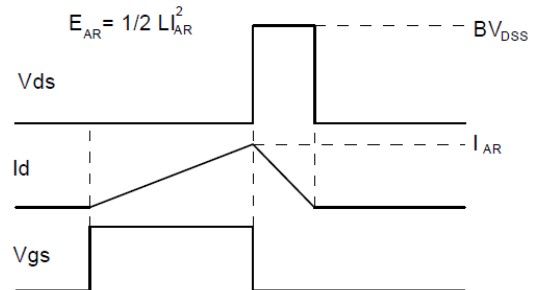
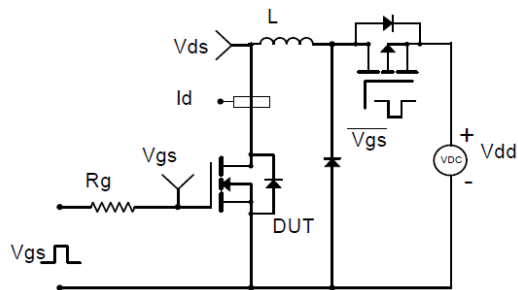
Resistive Switching Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Gate Charge Test Circuit & Waveform

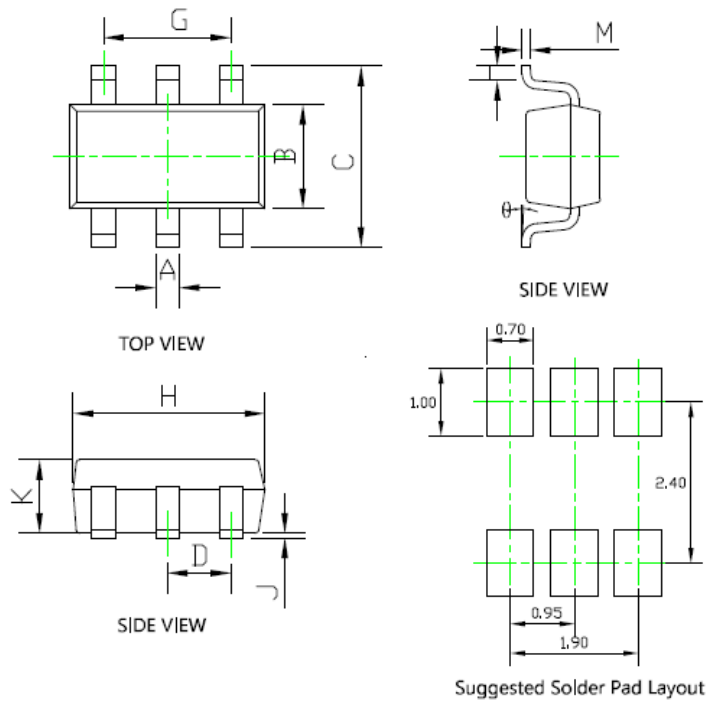


Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



YJS03N10A

■SOT-23-6L Package information



Note:
1. Controlling dimension in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.

SYMBOL	DIMENSIONS			
	INCHES		Millimeter	
	MIN.	MAX.	MIN.	MAX.
A	0.012	0.020	0.300	0.500
B	0.059	0.067	1.500	1.700
C	0.104	0.116	2.650	2.950
D	0.037BSC		0.950BSC	
G	0.075BSC		1.900BSC	
H	0.111	0.119	2.820	3.020
J	0.000	0.004	0.000	0.100
K	0.041	0.045	1.050	1.150
L	0.012	0.024	0.300	0.600
M	0.004	0.008	0.100	0.200
θ	0°	8°	0°	8°



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